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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>				Application Number	10-723,714
				Filing Date	
				First Named Inventor	Bing Ji, et al.
				Art Unit	1763
				Examiner Name	George Goudreau
Sheet	1	of	2	Attorney Docket Number	06299P2 USA

U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
	US-	2001/0011520 A1	8/9/2001	K. Doering, et al.	
	US-	2001/0055852 A1	12/27/2001	T. S. Moise, et al.	
	US-	5,288,662	2/24/1994	A. Lagendijk, et al.	
	US-	5,298,075	3/29/1994	A. Lagendijk, et al.	
	US-	5,356,478	10/18/1994	C. Chen, et al.	
	US-	5,454,903	10/3/1995	F. C. Redeker, et al.	
	US-	5,756,400	5/26/1998	Y. Ye, et al.	
	US-	5,879,459	3/9/1999	P. N. Gadgil, et al.	
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	US-	6,211,035	4/3/2001	T. S. Moise, et al.	
	US-	6,238,582	5/29/2001	K. E. Williams, et al.	
	US-	6,387,185	5/14/2002	K. Doering, et al.	
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FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
		Country Code ³ Number ⁴ Kind Code ⁵ (if known)				
	/	EP 1 001 459 A2	5/17/2000	Europe		<input checked="" type="checkbox"/>
	/	WO 00/40772	7/13/2000	World		<input checked="" type="checkbox"/>
	/	WO 00/79019 A1	12/28/2000	World		<input checked="" type="checkbox"/>
	/	WO 02/43114 A2	5/30/2002	World		<input checked="" type="checkbox"/>
	/	WO 02/43115 A2	5/30/2002	World		<input checked="" type="checkbox"/>

Examiner Signature	George Goudreau	Date Considered	5-041
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				First Named Inventor	Dingjun Wu, et al.
				Art Unit	1763
				Examiner Name	George Goudreau
Sheet	2	of	2	Attorney Docket Number	06469 USA

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
GAG	/	K. K. Shih, "Hafnium Dioxide Etch-Stop Layer for Phase-Shifting Masks," J. Vac. Sci. Technol. B 11(6), pp. 2130-2131(1993).	✓
	/	J. A. Britten, "Etch-Stop Characteristics of Sc ₂ O ₃ and HfO ₂ Films for...", J. Vac. Sci. Technol. A 14(5), pp. 2973-2975 (1996).	✓
	/	J. Hong, "Comparison of C ₁₂ and F ₂ Based Chemistries for the...", J. Vac. Sci. Technol. A 17(4), pp. 1326-1330 (1999).	✓
	/	J. W. Lee, "Electron Cyclotron Resonance Plasma Etching of Oxides...", J. Vac. Sci. Technol. A 16(3), pp. 1944-1948.	✓
	/	W. G. M. van den Hoek, "The Etch Mechanism for Al ₂ O ₃ in Fluorine and Chlorine Based RF Dry Etch Plasma," Mat. Res. Soc. Symp. Proc., 68, pp. 71-78 (1986).	✓
	/	J. E. Spencer, et al., "Emission Spectroscopy of CC14 and BC13 Plasma During Aluminum Etching," Proceedings—Electrochemical Society, 82-7, pp. 103-107 (1982).	✓
	/	T. Kanninen, et al., "Growth of Dielectric HfO ₂ /Ta ₂ O ₅ Thin Film Nanolaminate Capacitors by Atomic Layer Epitaxy," Proceedings—Electrochemical Society, 97-31, pp. 36-46 (1998).	✓
	/	H. B. Bell, et al., "Reactive Ion Etching of Aluminum/Silicon in BBr ₃ /Cl ₂ and BCl ₃ /Cl ₂ Mixtures," Journal of Electrochemical Society, 135(5), pp. 1184-91 (1988).	✓
	/	Y. S. Lee, et al., "Mass Spectrometric Characterization of BCl ₃ /SF ₆ Plasmas," Journal of Applied Physics, 88(8), pp. 4507-4509 (1980).	✓
	/	N. Heiman, et al., "High Rate Reactive Ion Etching of Al ₂ O ₃ and Si," J. Vac. Sci. Technol., 17(3), pp. 731-734 (1980).	✓
GAG	/	K. Shibata, et al., "Manufacturing Method and its Equipment of Thin Film Magnetic Head," Japanese Patent Application JP2000251221A (2000).	✓
	/	J. Chen, et al., "Formation of Polycrystalline Silicon Germanium/HfO ₂ Gate Stack Structure Using Inductively Coupled Plasma Etching," J. Vac. Sci. Technol. A 21(4), pp. 1210-1217 (2003).	✓

Examiner Signature	George Goudreau	Date Considered	5-041
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